

8 GB DDR4 SDRAM UDIMM Specification

Specifications

Max. Speed; CAS Latency	DDR4-3200@CL=22
Row Cycle Time (tRCmin)	45.75 ns
Refresh to Active/Refresh Command Time (tRFCmin)	350 ns(min.)
Row Active Time (tRASmin)	32 ns(min.)
Operating Temperature	0 °C to +85 °C
Storage Temperature (T _{STG})	-55 to 100 °C

Features

- 288-pin, unbuffered dual in-line memory module (UDIMM)
- 1Rx8 memory module (1 rank of x8 DDR4 SDRAMs)
- Power supply:
 - VDD = VDDQ = 1.2 V $\pm$ 5%
 - VPP = 2.5 V $-5\%/+10\%$
 - VDDSPD = 2.2 V to 3.6 V
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Low-power auto self refresh (LPASR)
- Data bus inversion (DBI) for data bus
- On-die VREFDQ generation and calibration
- On-board I²C serial presence-detect (SPD) EEPROM
- 16 internal banks; 4 groups of 4 banks each
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- Fly-by topology
- Terminated control command and address bus
- PCB Height: 1.23" (31.25 mm)



Change History			
Document No.: DSA6F8GH3SBAAMCF.(Rev.#)			
Rev. #	Who	When	What
01	Rik	2023-05-04	Initial version derived from DSA6F8GH3SBAAZF.04; Updated header and footer